- Designed for High-Speed Multipoint Data Transmission Over Long Cables
- Operates With Pulse Widths as Low as 30 ns
- Low Supply Current . . . 5 mA Max
- Meets or Exceeds the Standard Requirements of ANSI RS-485 and ISO 8482:1987(E)
- Common-Mode Voltage Range of –7 V to 12 V
- Positive- and Negative-Output Current Limiting
- Driver Thermal Shutdown Protection
- Pin Compatible With the SN75179B

#### description

The SN65LBC179. SN65LBC179Q. and SN75LBC179 differential driver and receiver pairs are monolithic integrated circuits designed for bidirectional data communication over long cables that take on the characteristics of transmission lines. They are balanced, or differential, voltage mode devices that meet or exceed the requirements of industry standards ANSI RS-485 and ISO 8482:1987(E). Both devices are designed using TI's proprietary LinBiCMOS<sup>™</sup> with the low power consumption of CMOS and the precision and robustness of bipolar transistors in the same circuit.

The SN65LBC179, SN65LBC179Q, and SN75LBC179 combine a differential line driver and differential line receiver and operate from a single 5-V supply. The driver differential outputs and the receiver differential inputs are connected to separate terminals for full-duplex operation and are designed to present minimum loading to the bus when powered off ( $V_{CC} = 0$ ). These parts feature a wide common-mode voltage range making them suitable for point-to-point or multipoint data bus applications. The devices also provide positive- and negative-current limiting and thermal shutdown for protection from line fault conditions. The line driver shuts down at a junction temperature of approximately 172°C.



D OR P PACKAGE (TOP VIEW)							
V <sub>CC</sub> [	1	υ	8	] A			
R [	2		7	] B			
D [	3		6	] Z			
GND [	4		5	] Y			

#### **Function Tables**

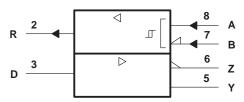
D	RIVER

INPUT	OUTPUTS					
D	ΥZ					
Н	ΗL					
L	LH					

DIFFERENTIAL INPUTS A-B	OUTPUT R
$V_{ID} \ge 0.2 V$	Н
$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$	?
$V_{ID} \leq -0.2 V$	L
Open circuit	Н

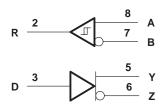
H = high level, L = low level, ? = indeterminate

#### logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

### logic diagram (positive logic)





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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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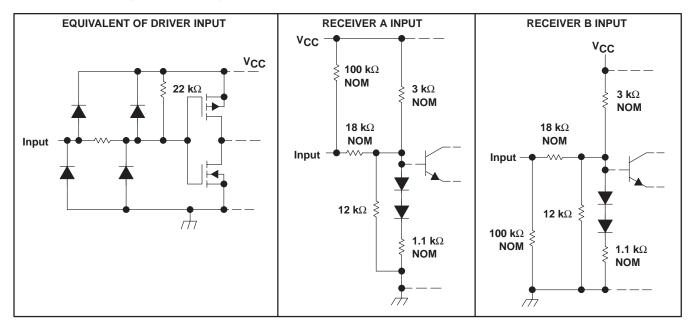
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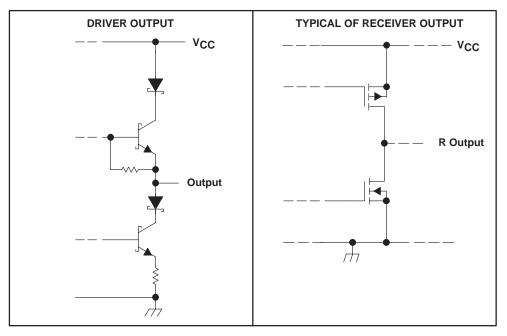
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#### description (continued)

The SN65LBC179, SN65LBC179Q, and SN75LBC179 are available in the 8-pin dual-in-line and small-outline packages. The SN75LBC179 is characterized for operation over the commercial temperature range of 0°C to 70°C. The SN65LBC179 is characterized over the industrial temperature range of -40°C to 85°C. The SN65LBC179Q is characterized over the extended industrial or automotive temperature range of -40°C to 125°C.

### schematics of inputs and outputs







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#### absolute maximum ratings<sup>†</sup>

Supply voltage range, V <sub>CC</sub>	
Voltage range at D or R (see Note 1)	
Receiver output current, I <sub>O</sub>	±10 mA
Continuous total power dissipation (see Note 2)	Internally limited
Total power dissipation	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

2. The maximum operating junction temperature is internally limited. Uses the dissipation rating table to operate below this temperature.

		MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>		4.75	5	5.25	V
High-level input voltage, VIH	D	2			V
Low-level input voltage, VIL	D			0.8	V
Differential input voltage, VID		-6‡		6	V
Voltage at any bus terminal (separately or common-mode), $V_{\mbox{O}},V_{\mbox{I}},orV_{\mbox{IC}}$	A, B, Y, or Z	-7		12	V
Rele lovel extend extended love	Y or Z			-60	
High-level output current, IOH	R			-8	mA
	Y or Z			60	
Low-level output current, IOL	R			8	mA
Junction temperature, TJ	•			140	°C
	SN65LBC179	-40		85	
High-level input voltage, V <sub>IH</sub> Low-level input voltage, V <sub>IL</sub> Differential input voltage, V <sub>ID</sub> Voltage at any bus terminal (separately or common-mode), V <sub>O</sub> , V <sub>I</sub> , or V <sub>IC</sub> High-level output current, I <sub>OH</sub> Low-level output current, I <sub>OL</sub>	SN65LBC179Q	-40		125	°C
	SN75LBC179	0		70	

#### recommended operating conditions

The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this data sheet for differential input voltage, voltage at any bus terminal (separately or common mode), operating temperature, input threshold voltage, and common-mode output voltage.

#### DISSIPATION RATING TABLE

PACKAGE	THERMAL MODEL	<b>A 1 1 1</b>		T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING
	Low K†	526 mW	5.0 mW/°C	301 mW	226 mW
D	High K‡	882 mW	8.4 mW/°C	504 mW	378 mW
Р		840 mW	8.0 mW/°C	480 mW	360 mW

<sup>†</sup> In accordance with the low effective thermal conductivity metric definitions of EIA/JESD 51–3.

<sup>‡</sup> In accordance with the high effective thermal conductivity metric definitions of EIA/JESD 51–7.



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### DRIVER SECTION

#### electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS	MIN	TYP†	MAX	UNIT
VIK	Input clamp voltage	I <sub>I</sub> = – 18 mA				-1.5	V
		$R_L = 54 \Omega$ ,	SN65LBC179, SN65LBC179Q	1.1	2.2	5	
		See Figure 1	SN75LBC179	1.5	2.2	5	
IVOD	$ V_{OD} $ Differential output voltage (see Note 3) R <sub>L</sub> = 60 $\Omega$ , See Figure 2	SN65LBC179, SN65LBC179Q	1.1	2.2	5	V	
		See Figure 2	SN75LBC179	1.5	2.2	5	
$\Delta  V_{OD} $	Change in magnitude of differential output voltage (see Note 4)	See Figures 1 and 2				±0.2	V
Voc	Common-mode output voltage			1	2.5	3	V
∆ V <sub>OC</sub>	Change in magnitude of common-mode output voltage (see Note 4)	$R_L = 54 \Omega$ , See Figure 1				±0.2	V
IO	Output current with power off	$V_{CC} = 0,$	$V_{O} = -7 V$ to 12 V			±100	μΑ
ΙΗ	High-level input current	V <sub>I</sub> = 2.4 V				-100	μΑ
١ <sub>IL</sub>	Low-level input current	V <sub>I</sub> = 0.4 V				-100	μA
IOS	Short-circuit output current	$-7 \text{ V} \le \text{V}_{O} \le 12 \text{ V}$				±250	mA
ICC	Supply current	No load	SN65LBC179, SN75LBC179		4.2	5	mA
			SN65LBC179Q		4.2	7	mA

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25^{\circ}\text{C}$ .

NOTES: 3. The minimum V<sub>OD</sub> specification of the SN65179 may not fully comply with ANSI RS-485 at operating temperatures below 0°C. System designers should take the possibly lower output signal into account in determining the maximum signal transmission distance.

4. Δ|V<sub>OD</sub>| and Δ|V<sub>OC</sub>| are the changes in the steady-state magnitude of V<sub>OD</sub> and V<sub>OC</sub>, respectively, that occur when the input is changed from a high level to a low level.

### switching characteristics, $V_{CC} = 5 V$ , $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
<sup>t</sup> d(OD)	Differential-output delay time	R <sub>L</sub> = 54 Ω,	Soo Figuro 2	7	18	ns
<sup>t</sup> t(OD)	Differential transition time		See Figure 3	5	20	ns



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### **RECEIVER SECTION**

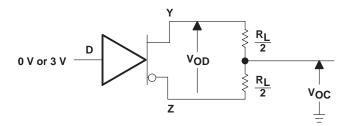
#### electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST	CONDIT	IONS	MIN	TYP	MAX	UNIT
$V_{IT+}$	Positive-going input threshold voltage	I <sub>O</sub> = -8 mA	I <sub>O</sub> = -8 mA				0.2	V
VIT-	Negative-going input threshold voltage	I <sub>O</sub> = 8 mA	I <sub>O</sub> = 8 mA					V
V <sub>hys</sub>	Hysteresis voltage (VIT + - VIT -)					45		mV
VOH	High-level output voltage	V <sub>ID</sub> = 200 mV,	IOH =	= – 8 mA	3.5	4.5		V
VOL	Low-level output voltage	$V_{ID} = -200 \text{ mV},$	IOL =	8 mA		0.3	0.5	V
		$V_{I} = 12 V$ , Other inputs at 0 V,		SN65LBC179, SN75LBC179		0.7	1	mA
		$V_{CC} = 5 V$		SN65LBC179Q		0.7	1.2	mA
		$V_{I} = 12 V$ , Other inputs at 0 V,		SN65LBC179, SN75LBC179		0.8	1	mA
	Rue input ourrest	VCC = 0 $V$		SN65LBC179Q		0.8	1.2	mA
łı	Bus input current	$V_{I} = -7 V$ , Other inputs at 0 V,		SN65LBC179, SN75LBC179		-0.5	-0.8	mA
		$V_{CC} = 5 V$		SN65LBC179Q		-0.5	-1.0	mA
		$V_I = -7 V$ , Other inputs at 0 V,		SN65LBC179, SN75LBC179		-0.5	-0.8	mA
		VCC = 0 V		SN65LBC179Q		-0.5	-1.0	mA

## switching characteristics, $V_{CC}$ = 5 V, $T_A$ = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> PHL	Propagation delay time, high- to low-level output		15		30	ns
<sup>t</sup> PLH	Propagation delay time, low- to high-level output	$V_{\text{ID}} = -1.5 \text{ V}$ to 1.5 V, See Figure 4	15		30	ns
t <sub>sk(p)</sub>	Pulse skew (	See Figure 4		3	6	ns
tt	Transition time	See Figure 4		3	5	ns

#### PARAMETER MEASUREMENT INFORMATION



#### Figure 1. Differential and Common-Mode Output Voltage Test Circuit



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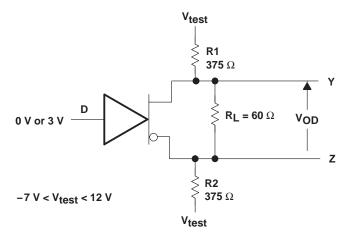
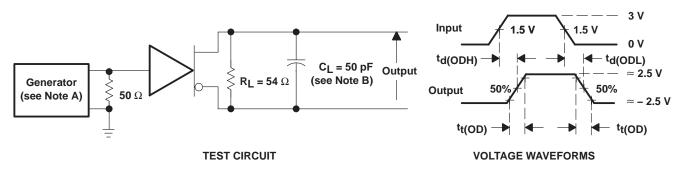
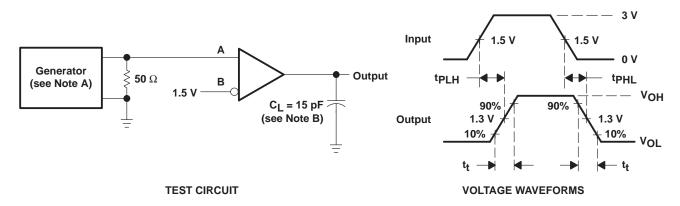


Figure 2. Differential Output Voltage Test Circuit



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle, t<sub>f</sub>  $\leq$  6 ns, t<sub>f</sub>  $\leq$  6 ns, Z<sub>O</sub> = 50  $\Omega$ .
  - B. CL includes probe and jig capacitance.

Figure 3. Driver Test Circuits and Differential Output Delay and Transition Time Voltage Waveforms

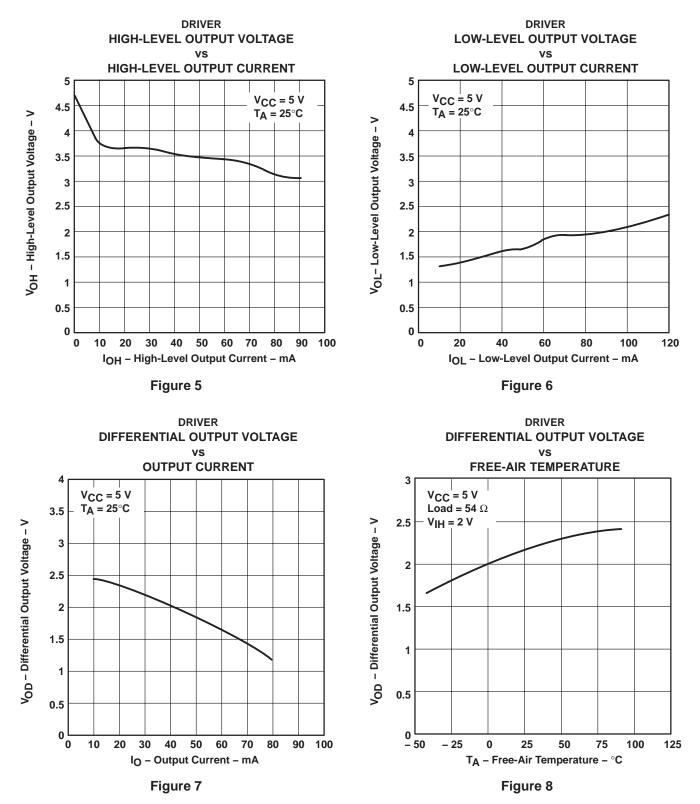


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle, t<sub>f</sub>  $\leq$  6 ns, t<sub>f</sub>  $\leq$  6 ns, Z<sub>O</sub> = 50  $\Omega$ .
  - B. CL includes probe and jig capacitance.

Figure 4. Receiver Test Circuit and Propagation Delay and Transition Time Voltage Waveforms



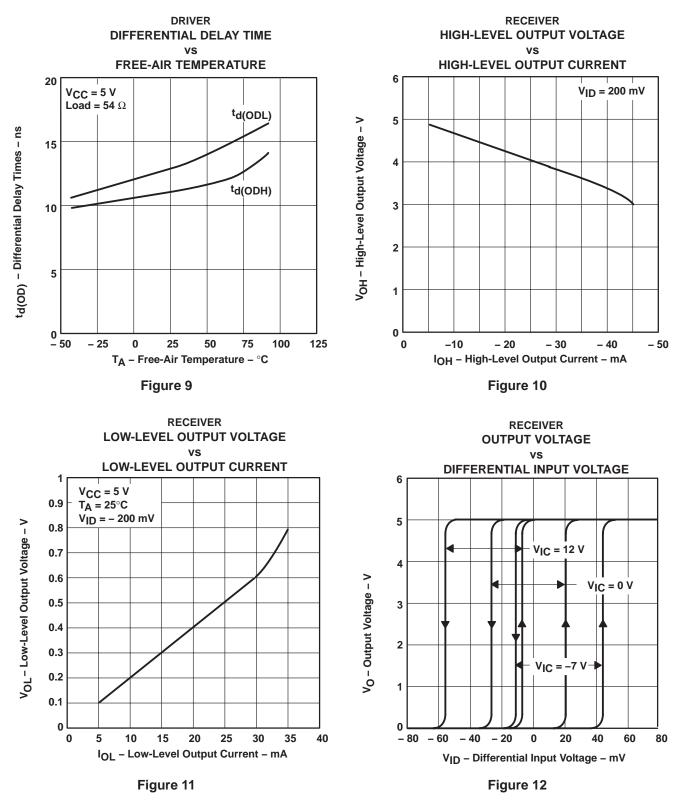
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#### **TYPICAL CHARACTERISTICS**



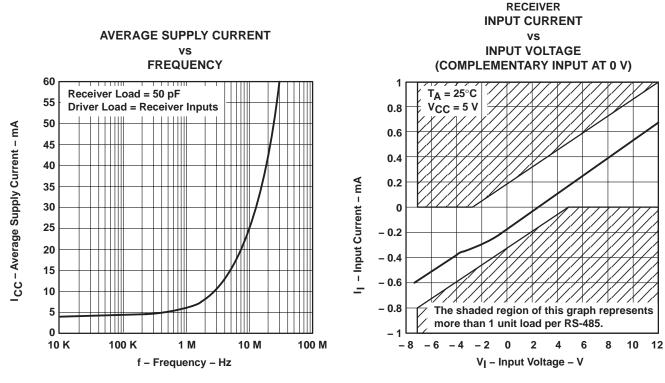
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#### **TYPICAL CHARACTERISTICS**



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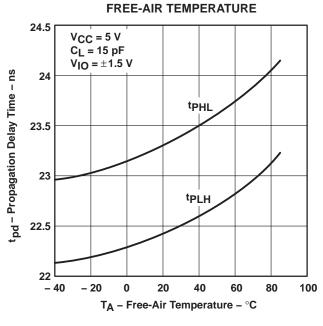


### **TYPICAL CHARACTERISTICS**

Figure 13



RECEIVER PROPAGATION DELAY TIME vs







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THERMAL CHARACTERISTICS – D PACKAGE								
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
lumetion to embiant thermal relation of 0, 1	Low-K board, no air flow		199.4					
Junction–to–ambient thermal reisistance, $\theta_{JA}^{\dagger}$	High-K board, no air flow	119 67 46.6						
Junction–to–board thermal reisistance, $\theta_{JB}$	High-K board, no air flow				°C/W			
Junction–to–case thermal reisistance, $\theta_{JC}$								
Average power dissipation, P(AVG)	R <sub>L</sub> = 54 Ω, input to D is 10 Mbps 50% duty cycle square wave, V <sub>CC</sub> = 5.25 V, T <sub>J</sub> = 130 °C.			330	mW			
Thermal shutdown junction temperature, $T_{SD}$			165		°C			

<sup>†</sup> See TI application note literature number SZZA003, Package Thermal Characterization Methodologies, for an explanation of this parameter.



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### THERMAL CHARACTERISTICS OF IC PACKAGES

 $\Theta_{JA}$  (Junction-to-Ambient Thermal Resistance) is defined as the difference in junction temperature to ambient temperature divided by the operating power

 $\Theta_{\text{JA}}$  is NOT a constant and is a strong function of

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

 $\Theta_{JA}$  can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures.  $_{\Theta JA}$  is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives *average* in-use condition thermal performance and consists of a single trace layer 25 mm long and 2-oz thick copper. The high-k board gives *best case* in–use condition and consists of two 1-oz buried power planes with a single trace layer 25 mm long with 2-oz thick copper. A 4% to 50% difference in  $\Theta_{JA}$  can be measured between these two test cards

 $\Theta_{JC}$  (Junction-to-Case Thermal Resistance) is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

 $\Theta_{JC}$  is a useful thermal characteristic when a heatsink is applied to package. It is NOT a useful characteristic to predict junction temperature as it provides pessimistic numbers if the case temperature is measured in a non-standard system and junction temperatures are backed out. It can be used with  $\Theta_{JB}$  in 1-dimensional thermal simulation of a package system.

 $\Theta_{JB}$  (Junction-to-Board Thermal Resistance) is defined to be the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold–plate structure.  $\Theta_{JB}$  is only defined for the high-k test card.

 $\Theta_{JB}$  provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system (see Figure 16).

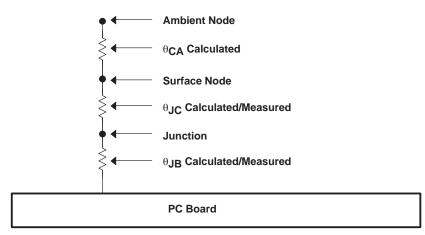


Figure 16. Thermal Resistance





6-Feb-2020

## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LBC179D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB179	Samples
SN65LBC179DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB179	Samples
SN65LBC179DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB179	Samples
SN65LBC179P	ACTIVE	PDIP	Ρ	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type	-40 to 85	65LBC179	Samples
SN65LBC179QD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB179Q	Samples
SN65LBC179QDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB179Q	Samples
SN65LBC179QDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB179Q	Samples
SN65LBC179QDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB179Q	Samples
SN75LBC179D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	7LB179	Samples
SN75LBC179DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	7LB179	Samples
SN75LBC179DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	7LB179	Samples
SN75LBC179P	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type	0 to 70	75LBC179	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.



# PACKAGE OPTION ADDENDUM

6-Feb-2020

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LBC179DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LBC179QDR	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN75LBC179DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

18-Oct-2016



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LBC179DR	SOIC	D	8	2500	340.5	338.1	20.6
SN65LBC179QDR	SOIC	D	8	2500	340.5	338.1	20.6
SN75LBC179DR	SOIC	D	8	2500	340.5	338.1	20.6

# D0008A



# **PACKAGE OUTLINE**

### SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



# D0008A

# **EXAMPLE BOARD LAYOUT**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## D0008A

# **EXAMPLE STENCIL DESIGN**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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